



General Description

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.



SMAF

Features

- Low conduction loss due to low V_F
- Extremely low switching loss by tiny Q_c
- Highly rugged due to better surge current
- Industrial standard quality and reliability



Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction



Part Number	Package	Brand
H1D02065AF	SMAF	HXY MOSFET

Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V_{RRM}	Repetitive Peak Reverse Voltage	650	V	
V_{RSM}	Surge Peak Reverse Voltage	650	V	
V_R	DC Peak Reverse Voltage	650	V	
I_F	Continuous Forward Current	6 3 2	A	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=152^\circ\text{C}$
I_{FRM}	Repetitive Peak Forward Surge Current	12 8	A	$T_c=25^\circ\text{C}, t_p=10\text{ ms, Half Sine Pulse}$ $T_c=110^\circ\text{C}, t_p=10\text{ ms, Half Sine Pulse}$
I_{FSM}	Non-Repetitive Forward Surge Current	18 14	A	$T_c=25^\circ\text{C}, t_p=10\text{ ms, Half Sine Pulse}$ $T_c=110^\circ\text{C}, t_p=10\text{ ms, Half Sine Pulse}$
P_{tot}	Power Dissipation	12 8	W	$T_c=25^\circ\text{C}$ $T=110^\circ\text{C}$
$\int i^2 dt$	$i^2 t$ value	1.62 0.98	A^2s	$T_c=25^\circ\text{C}, t_p=10\text{ ms}$ $T_c=110^\circ\text{C}, t_p=10\text{ ms}$
T_J	Operating Junction Range	-55 to +175	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$	



Electrical Characteristics

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Forward Voltage	V_F	-	1.3	1.5	V	$I_F=2A$
		-	1.5			$T_j=25^\circ C$
Reverse Current	I_R	-	2	50	μA	$V_R=650V$
		-	40	150		$T_j=25^\circ C$
Total Capacitive Charge	Q_C	-	3.7	-	nC	$V_R=400V, T_j=25^\circ C$
		-				$Q_C = \int_0^{V_R} C(V)dV$
Total Capacitance	C	-	181	-	pF	$T_j=25^\circ C, f=1MHz$
		-	10	-		$V_R=0V$
		-	8	-		$V_R=200V$
						$V_R=400V$

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	7.7	°C/W

Characteristics Curve

Fig 1: Forward Characteristics

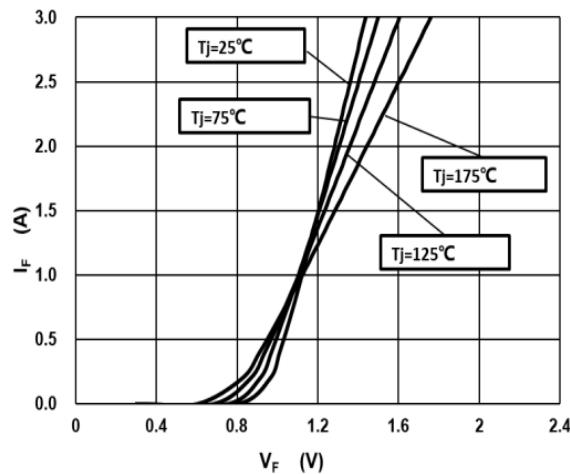


Fig 2: Reverse Characteristics

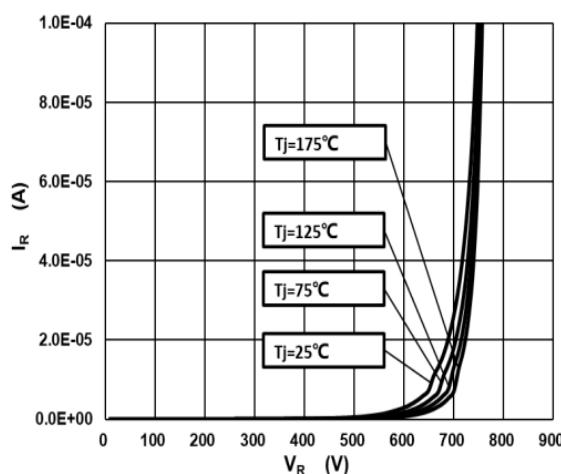




Fig 3: Current Derating

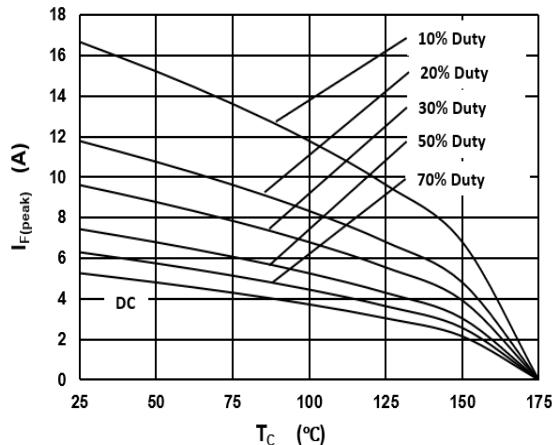


Fig 4: Power Derating

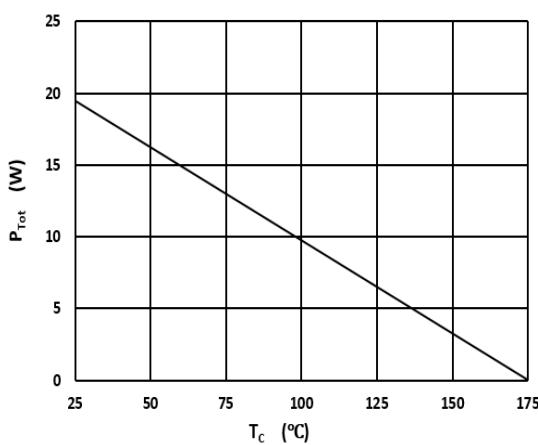


Fig 5: Capacitance vs. Reverse Voltage

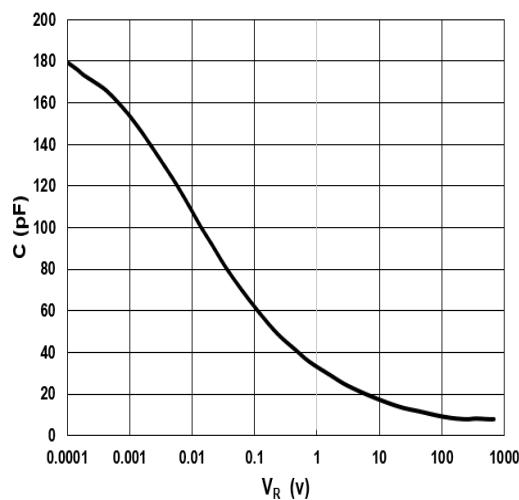


Fig 6: Reverse Charge vs. Reverse Voltage

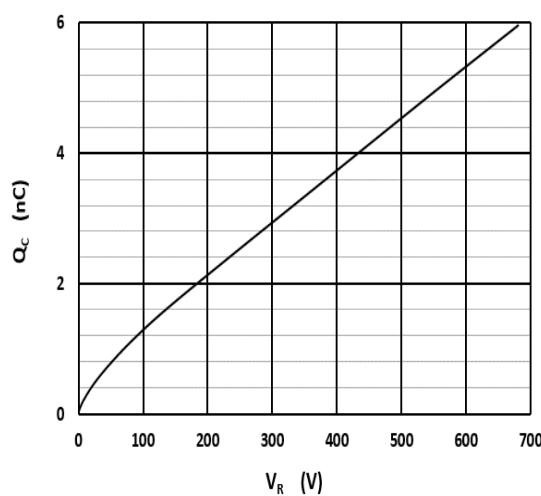


Fig 7: Typical Capacitance Stored Energy

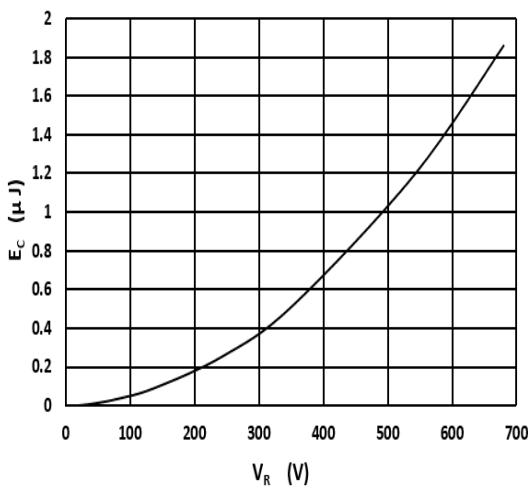
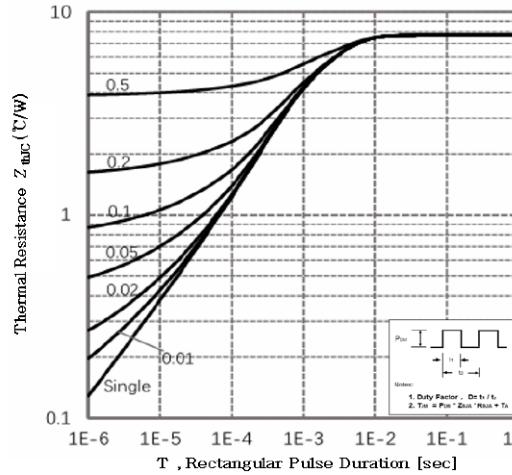
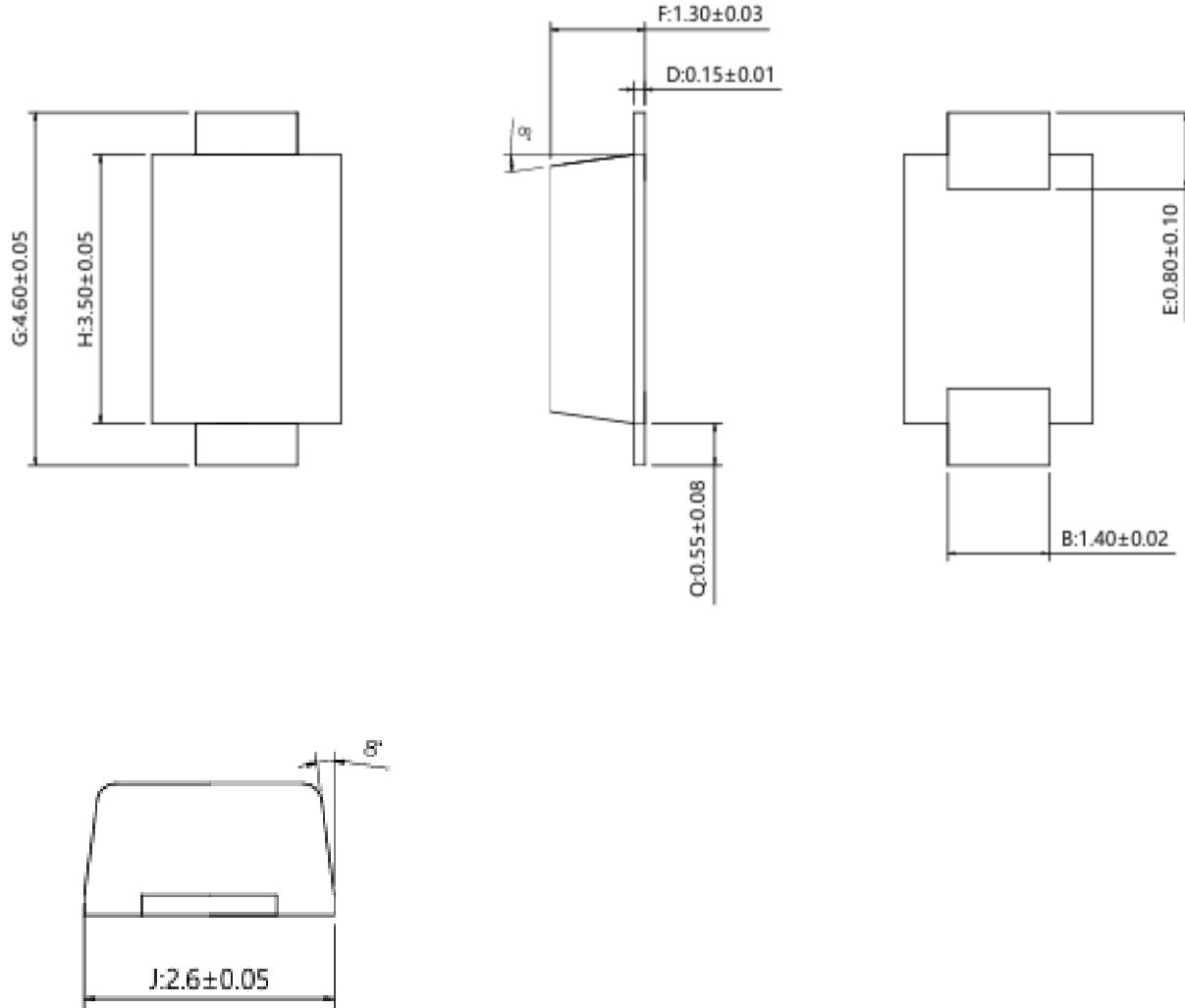


Fig 8: Transient Thermal Impedance





Package Information SMAF





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